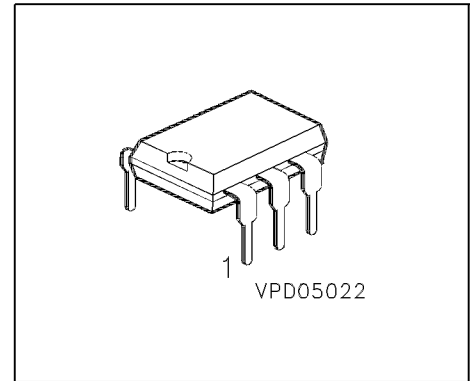


### SITAC® AC Switches Without Zero Voltage Switch

- AC switch with zero-voltage detector
- Electrically insulated between input and output circuit
- Microcomputer-compatible by very low trigger current
- UL-tested (file no. E 52744), code letter "J"
- Available with the following options:
  - Option 1: VDE 0884-approved
  - Option 6: Pins in 10.16 mm spacing
  - Option 7: Pins for surface mounting



Type	Opt.	V <sub>DRM</sub>	I <sub>TRMS</sub>	I <sub>FT</sub>	dv/dt <sub>cr</sub>	Marking	Ordering Code
BRT 11 H	-	400 V	300 mA	2 mA	10 kV/μs	BRT 11 H	C67079-A1000-A6
BRT 11 M	-	400 V	300 mA	3 mA	10 kV/μs	BRT 11 M	C67079-A1000-A10
BRT 12 H	-	600 V	300 mA	2 mA	10 kV/μs	BRT 12 H	C67079-A1001-A6
BRT 12 H	1	600 V	300 mA	2 mA	10 kV/μs	BRT 12 H	C67079-A1041-A5
BRT 12 H	6	600 V	300 mA	2 mA	10 kV/μs	BRT 12 H	C67079-A1041-A8
BRT 12 H	7	600 V	300 mA	2 mA	10 kV/μs	BRT 12 H	C67079-A1041-A11
BRT 12 H	1 + 6	600 V	300 mA	2 mA	10 kV/μs	BRT 12 H	C67079-A1041-A14
BRT 12 M	-	600 V	300 mA	3 mA	10 kV/μs	BRT 12 M	C67079-A1001-A10
BRT 12 M	1	600 V	300 mA	3 mA	10 kV/μs	BRT 12 M	C67079-A1041-A6
BRT 13 H	-	800 V	300 mA	2 mA	10 kV/μs	BRT 13 H	C67079-A1002-A6
BRT 13 H	6	800 V	300 mA	2 mA	10 kV/μs	BRT 13 H	C67079-A1042-A8
BRT 13 H	7	800 V	300 mA	2 mA	10 kV/μs	BRT 13 H	C67079-A1042-A11
BRT 13 M	-	800 V	300 mA	3 mA	10 kV/μs	BRT 13 M	C67079-A1002-A10

Information	Package	Pin Configuration					
		1	2	3	4	5	6
50 pcs per tube	P-DIP-6	Anode	Cathode	not connected	A1	do not connect	A2

**Maximum Ratings**, at  $T_j = 25\text{ °C}$ , unless otherwise specified.

### AC Switch

Parameter	Symbol	Value	Unit
Max. Power dissipation	$P_{\text{tot}}$	630	mW
Chip or operating temperature	$T_j$	-40 ...+ 100	°C
Storage temperature	$T_{\text{stg}}$	-40 ...+ 150	
Insulation test voltage <sup>1)</sup> between input/output circuit (climate in acc. with DIN 40046, part2, Nov.74)	$V_{\text{IS}}$	5300	$V_{\text{RMS}}$
Reference voltage in acc. with VDE 0110 b (insulation group C)	$V_{\text{ref}}$	500 600	$V_{\text{RMS}}$ $V_{\text{DC}}$
Creepage tracking resistance (in acc. with DIN IEC 112/VDE 0303, part 1)	$C_{\text{TI}}$	175	(group IIIa acc. to DIN VDE 0109)
Insulation resistance $V_{\text{IO}} = 500\text{ V}$ , $T_A = 25\text{ °C}$ $V_{\text{IO}} = 500\text{ V}$ , $T_A = 100\text{ °C}$	$R_{\text{is}}$	$\geq 10^{12}$ $\geq 10^{11}$	$\Omega$
DIN humidity category, DIN 40 040	-	F	-
Creepage distance (input/output circuit)	-	$\geq 7.2$	mm
Clearance (input/output circuit)	-	$\geq 7.2$	

### Input Circuit

Parameter	Symbol	Value	Unit
Param VR	$V_R$	6	V
Continuous forward current	$I_F$	20	mA
Surge forward current	$I_{\text{FSM(I)}}$	1.5	A
Max. power dissipation, $t \leq 10\text{ }\mu\text{s}$	$P_{\text{tot}}$	30	mW

### Output Circuit

Parameter	Symbol	BRT	BRT	BRT	Unit
		11	12	13	
Repetitive peak off-state voltage	$V_{\text{DRM}}$	400	600	800	V
RMS on-state current	$I_{\text{TRMS}}$	300			mA
Single cycle surge current (50 Hz)	$I_{\text{TSM(I)}}$	3			A
Max. power dissipation	$P_{\text{tot}}$	600			mW

### Characteristics

at  $T_j = 25\text{ °C}$ , unless otherwise specified.

### Input Circuit

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Forward Voltage, $I_F = 10\text{ mA}$	$V_F$	-	1.1	1.35	V
Reverse current, $V_R = 6\text{ V}$	$I_R$	-	-	10	$\mu\text{A}$
Thermal resistance 2) junction - ambient	$R_{thJA}$	-	-	750	K/W

### Output Circuit

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Critical rate of rise of off-state voltage $V_D = 0.67 V_{DRM}, T_j = 25\text{ °C}$ $V_D = 0.67 V_{DRM}, T_j = 80\text{ °C}$	$dv/dt_{cr}$	10 5	- -	- -	$\text{kV}/\mu\text{s}$
Critical rate of rise of voltage at current commutation $V_D = 0.67 V_{DRM}, T_j = 25\text{ °C}, di/dt_{crq} \leq 15\text{ A/ms}$ $V_D = 0.67 V_{DRM}, T_j = 80\text{ °C}, di/dt_{crq} \leq 15\text{ A/ms}$	$dv/dt_{crq}$	10 5	- -	- -	
Critical rate of rise of on-state current	$di/dt_{cr}$	8	-	-	$\text{A}/\mu\text{s}$
Pulse current $t_p \leq 5\text{ }\mu\text{s}, f = 100\text{ Hz}, di_{tp}/dt \leq 8\text{ A}/\mu\text{s}$	$I_{tp}$	-	-	2	A
On-state voltage, $I_T = 300\text{ mA}$	$V_T$	-	-	2.3	V
Off-state current $T_C = 100\text{ °C}, V_{DRM}$	$I_D$	-	0.5	100	$\mu\text{A}$
Holding current, $V_D = 10\text{ V}$	$I_H$	-	80	500	
Thermal resistance 2) junction - ambient	$R_{thJA}$	-	-	125	K/W

### Response Characteristics

at  $T_j = 25\text{ °C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Trigger current $V_D = 10\text{ V}$ type H type M	$I_{FT}$	0.4 0.8	- -	2 3	mA
Trigger current temperature gradient	$\Delta I_{FT}/\Delta T_j$	-	7	14	$\mu\text{A/K}$
Capacitance between input and output circuit $V_R = 0\text{ V}$ , $f = 1\text{ kHz}$	$C_{IO}$	-	-	2	pF

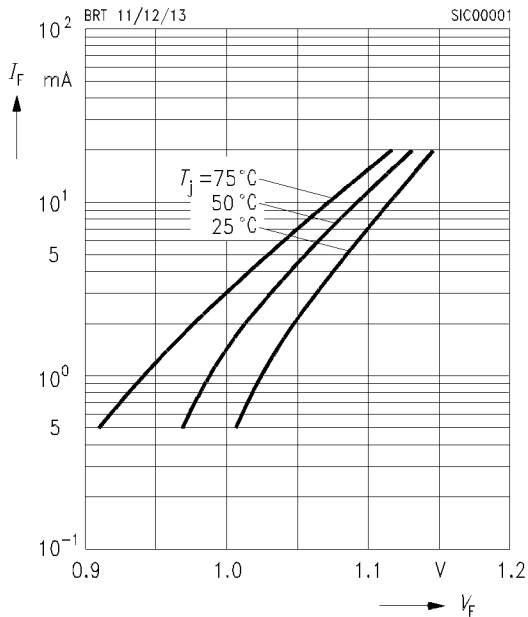
- 1) Test AC voltage in acc. with DIN 57883, June 1980
- 2) Static air, SITAC soldered in pcb or base plate.
- 3) The SITAC switch is soldered in pcb or base plate.
- 4) Thermocouple measurement has to be performed potentially separated to A1 and A2. The measuring junction should be as near as possible at the case.

### Characteristics

at  $T_j = 25\text{ °C}$ , unless otherwise specified.

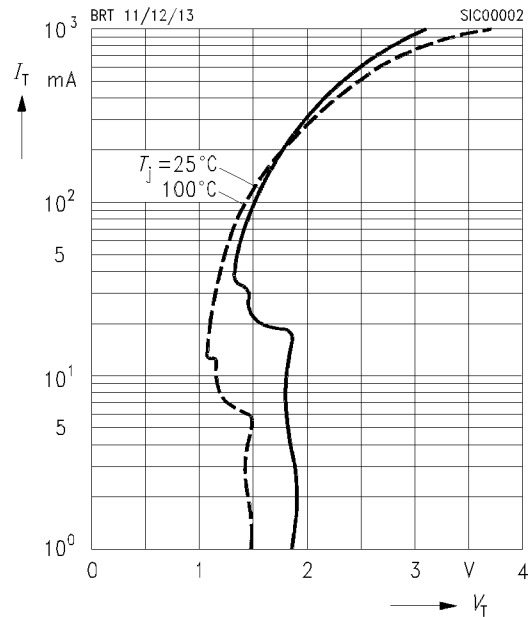
#### Typical input characteristics

$$I_F = f(V_F)$$



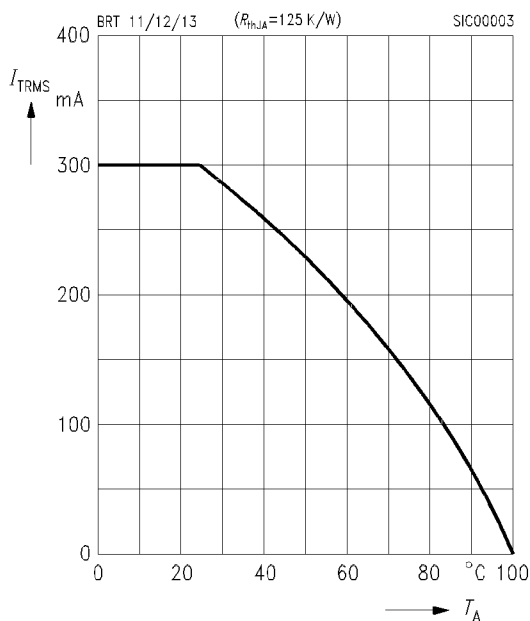
#### Typical output characteristics

$$I_T = f(V_T)$$



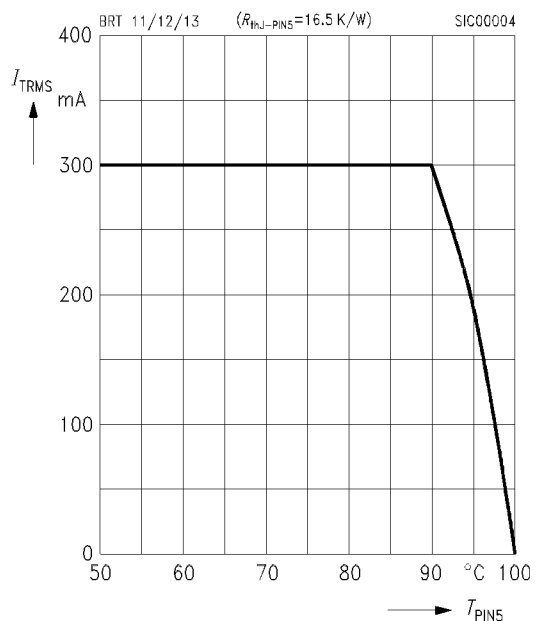
#### Current reduction $I_{TRMS} = f(T_A)$

$$R_{thJA} = 125\text{ K/W }^3)$$

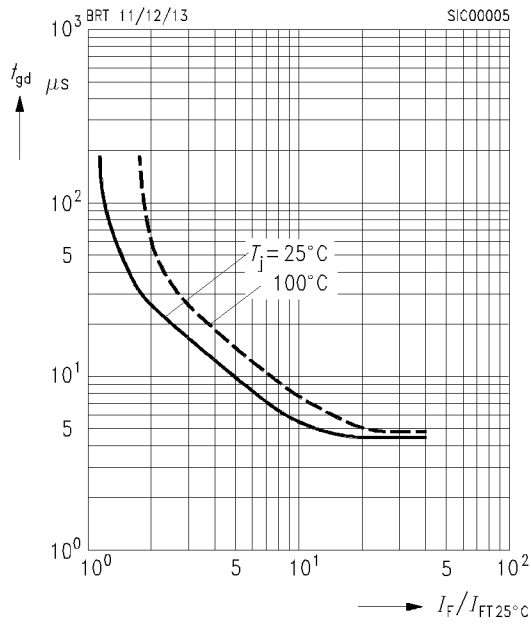


#### Current reduction $I_{TRMS} = f(T_{PIN5})$

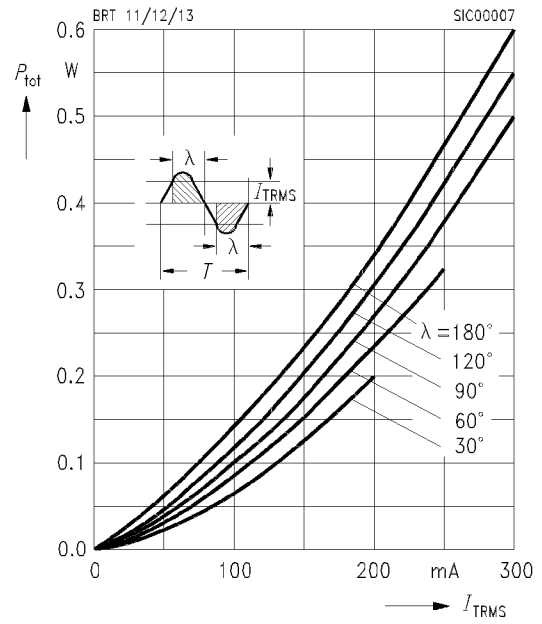
$$R_{thJ-PIN5} = 16,5\text{ K/W }^4)$$



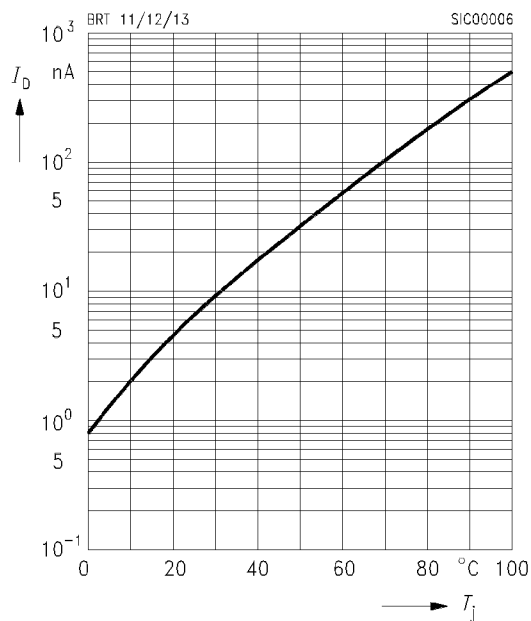
**Typical trigger delay time**  $t_{gd} = f(I_F/I_{FT25^\circ C})$   
 $V_D = 200V$



**Power dissipation for 40 ... 60 Hz line operation**  
 $P_{tot} = f(I_{TRMS})$



**Typical off-state current**  $I_D = f(T_j)$   
 $V_D = 800V$



**Pulse trigger current**  $I_{FTN} = f(t_{pIF})$   
 $I_{FTN}$  normalized to  $I_{FT}$  referring to  $t_{pIF} \geq 1 ms$   
 $V_{op} = 220 V, f = 40 \dots 60 Hz typ.$

